Supporting Information of "Superconductivity in Single-Quintuple-Layer Bi₂Te₃ Grown on Epitaxial FeTe"

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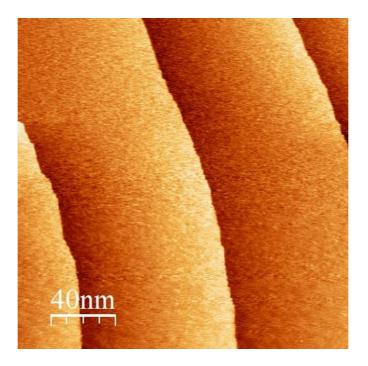


Figure S1: STM topographic image of SrTiO₃(001) surface after the annealing (size: 200 × 200 nm^2 , $V_{Bias} = 1.0 V$, $I_{Tunnel} = 200 pA$, color scale: 0.72 nm), representing an atomic flat surface with high dense atomic steps.

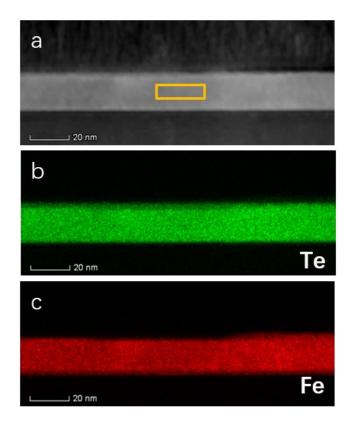


Figure S2: X-ray Energy Dispersive Spectroscopy (EDS) study on the Bi₂Te₃/FeTe bilayer. (a) the HAADF STEM image with area (marked by yellow box) selected for EDS counting. (b) & (c) the EDS mapping of Te and Fe element, respectively.

Element	Family	Atomic Fraction(%)	Atomic Error(%)
Fe	K	50	7.5
Te	K	50	9.1
Bi	К	0	0

Table S1: Atomic ratio of Fe and Te from EDS mapping results of area #1.

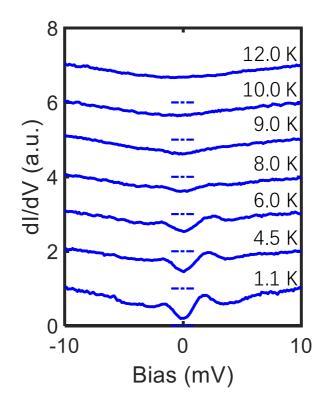


Figure S3: Temperature dependent dI/dV spectra acquired on the 2 QLs Bi₂Te₃ (set point: $V_{Bias} = 10 \ mV$, $I_{Tunnel} = 50 \ pA$). The Spectra are shifted vertically for clarity and the dashed line below each spectrum corresponds to the zero dI/dV value of the spectrum after vertical shift.

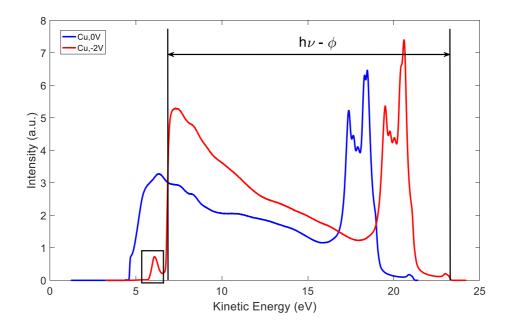


Figure S4: Ultra-violet photoelectron spectroscopy obtained from the Cu (111) surface. To verify the accuracy of the UPS method with calibration, we have measured the work function of clean Cu (111) surface and the results are shown above. Under a -2 V bias we successfully separated the secondary electrons generated in the spectrometer by impact, which has been highlighted in the figure by a rectangle. The width of the spectrum is indicated in the figure and we found that the working FWF is around 4.78 eV, which is consistent with the results from other groups.^{1–3}

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